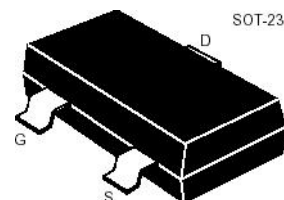


SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



## P-Channel Enhancement-Mode MOS FETs

P 沟道增强型 MOS 场效应管

### ■ MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$BV_{DSS}$	-50	V
Gate- Source Voltage 柵極-源極電壓	$V_{GS}$	$\pm 20$	V
Drain Current (continuous) 漏極電流-連續	$I_{DR}$	-130	mA
Drain Current (pulsed) 漏極電流-脈沖	$I_{DRM}$	-520	mA

### ■ THERMAL CHARACTERISTICS 熱特性

Characteristic 特性	Symbol 符號	Max 最大值	Unit 單位
Total Device Dissipation 總耗散功率 $T_A=25^\circ\text{C}$ 環境溫度為 $25^\circ\text{C}$ Derate above $25^\circ\text{C}$ 超過 $25^\circ\text{C}$ 遞減	$P_D$	200	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient 熱阻	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 結溫和儲存溫度	$T_J, T_{stg}$	150 $^\circ\text{C}$ , -55to+150 $^\circ\text{C}$	

### ■ DEVICE MARKING 打標

BSS84=PD

**■ ELECTRICAL CHARACTERISTICS 電特性**

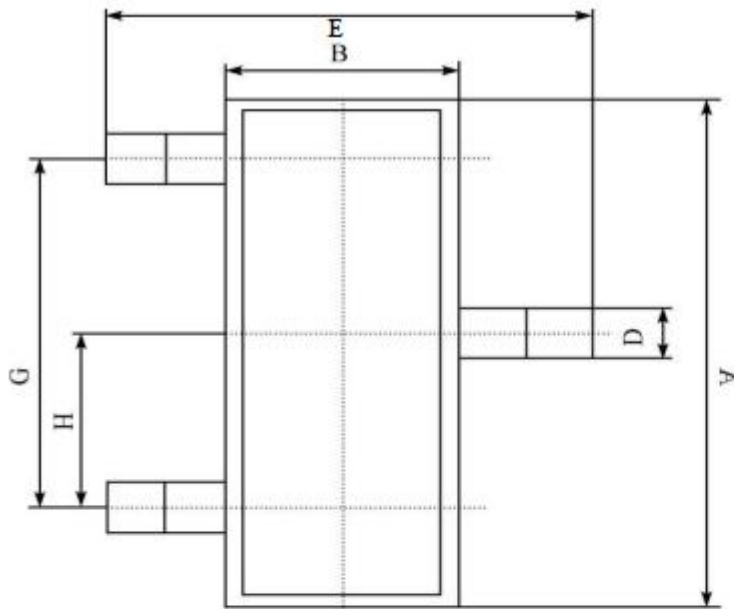
 (T<sub>A</sub>=25°C unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I <sub>D</sub> =-250uA, V <sub>GS</sub> =0V)	BV <sub>DSS</sub>	-50	—	—	V
Gate Threshold Voltage 柵極開啟電壓(I <sub>D</sub> =-250uA, V <sub>GS</sub> =V <sub>DS</sub> )	V <sub>GS(th)</sub>	-1.0	—	-2.5	V
Diode Forward Voltage Drop 內附二極管正向壓降(I <sub>SD</sub> =-200mA, V <sub>GS</sub> =0V)	V <sub>SD</sub>	—	—	-1.5	V
Zero Gate Voltage Drain Current 零柵壓漏極電流(V <sub>GS</sub> =0V, V <sub>DS</sub> =-50V) (V <sub>GS</sub> =0V, V <sub>DS</sub> =-50V, T <sub>A</sub> =125°C)	I <sub>DSS</sub>	—	—	-15 -60	uA
Gate Body Leakage 柵極漏電流(V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V)	I <sub>GSS</sub>	—	—	±10	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻(I <sub>D</sub> =-100mA, V <sub>GS</sub> =-5V)	R <sub>DS(ON)</sub>	—	—	10	Ω
Input Capacitance 輸入電容 (V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1MHz)	C <sub>ISS</sub>	—	73	—	pF
Common Source Output Capacitance 共源輸出電容(V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1MHz)	C <sub>OSS</sub>	—	10	—	pF
Turn-ON Time 開啟時間 (V <sub>DS</sub> =-30V, I <sub>D</sub> =-270mA, R <sub>GEN</sub> =6Ω)	t <sub>(on)</sub>	—	—	5	ns
Turn-OFF Time 關斷時間 (V <sub>DS</sub> =-30V, I <sub>D</sub> =-270mA, R <sub>GEN</sub> =6Ω)	t <sub>(off)</sub>	—	—	20	ns
Reverse Recovery Time 反向恢復時間 (I <sub>SD</sub> =-100mA, V <sub>GS</sub> =0V)	t <sub>rr</sub>	—	10	—	ns

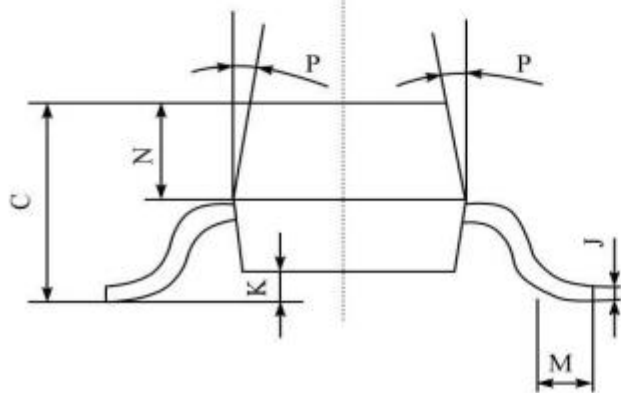
1. FR-5=1.0×0.75×0.062in.
2. Alumina=0.4×0.3×0.024in.99.5%alumina.
3. Pulse Width≤300 μ s; Duty Cycle≤2.0%.

■ DIMENSION 外形封裝尺寸

單位(UNIT): mm



代碼	範圍(單位:mm)
A	2.80~3.00
B	1.20~1.40
C	0.90~1.10
D	0.30~0.50
E	2.20~2.60
G	1.80~2.00
H	0.90~1.00
J	0.08~0.18
K	0.02~0.12
M	≥0.22
N	0.50~0.70
P	6°~10°



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